

ABSTRACT OF THE DISCLOSURE

The invention has for its objects to provide a multilayer thin film including a ferroelectric thin film having much more improved properties on an Si substrate and its fabrication

- 5 process as well as an electron device comprising the same. This object is achieved by the provision of a multilayer thin film formed on an Si substrate by epitaxial growth, which comprises a buffer layer formed on the Si substrate, which layer includes an oxide thin film, a perovskite oxide thin film formed on the
- 10 buffer layer, which film has a (100) or (001) orientation, and a ferroelectric thin film epitaxially grown on the perovskite oxide thin film and its fabrication process as well as an electron device comprising the same.

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